

TUNGSTEN SPUTTERING TARGET AND METHOD FOR PRODUCING SAME

ABSTRACT

5 A sputtering target containing 0.01 to 0.5 wt% of Ag, and remainder being W
and unavoidable impurities. The object of the present invention is to provide a
sputtering target capable of forming a film having a relatively low specific resistance
by sputtering, wherein the obtained film is endowed with good uniformity, and in
particular the sputtering target has superior characteristics upon forming thin films for
10 semiconductor devices, as well as to provide a method for producing the foregoing
sputtering target.